

Product Summary

BV_{DSS}	R_{DS(ON)} max	I_D T_C = +25°C (Note 9)
40V	3mΩ @ V _{GS} = 10V	100A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

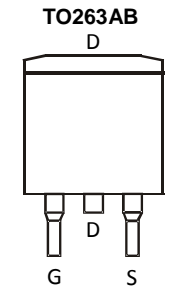
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMTH4004SCTBQ](#))**

Mechanical Data

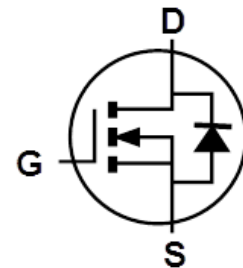
- Case: TO263AB
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓢ
- Weight: 1.4 grams (Approximate)



Top View



Pin Out Top View



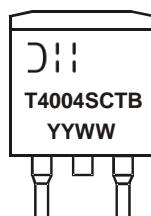
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4004SCTB-13	TO263AB	800 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



T4004SCTB = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 14 = 2014)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6)	I _D	T _C = +25°C (Note 9)	100
		T _C = +100°C	100
Maximum Continuous Body Diode Forward Current	I _S	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	200	A
Avalanche Current, L=0.2mH	I _{AS}	45	A
Avalanche Energy, L=0.2mH	E _{AS}	200	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	4.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	32	°C/W
Total Power Dissipation (Note 6)	P _D	136	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.5	3	mΩ	V _{GS} = 10V, I _D = 100A
Diode Forward Voltage	V _{SD}	—	—	1.3	V	V _{GS} = 0V, I _S = 100A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	4305	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oSS}	—	1441	—		
Reverse Transfer Capacitance	C _{rSS}	—	102	—		
Gate Resistance	R _G	—	0.77	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	68.6	—	nC	V _{DD} = 20V, I _D = 90A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	16.8	—		
Gate-Drain Charge	Q _{gd}	—	14.2	—		
Turn-On Delay Time	t _{D(ON)}	—	9.5	—	ns	V _{DD} = 20V, V _{GS} = 10V, I _D = 90A, R _G = 3.5Ω
Turn-On Rise Time	t _r	—	6.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	26.4	—		
Turn-Off Fall Time	t _f	—	8.1	—		
Reverse Recovery Time	t _{RR}	—	52.4	—	ns	I _F = 50A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	78.2	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 - Device mounted on infinite heatsink and measured by thermal couple attached on bottom heasink of package.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package limited.

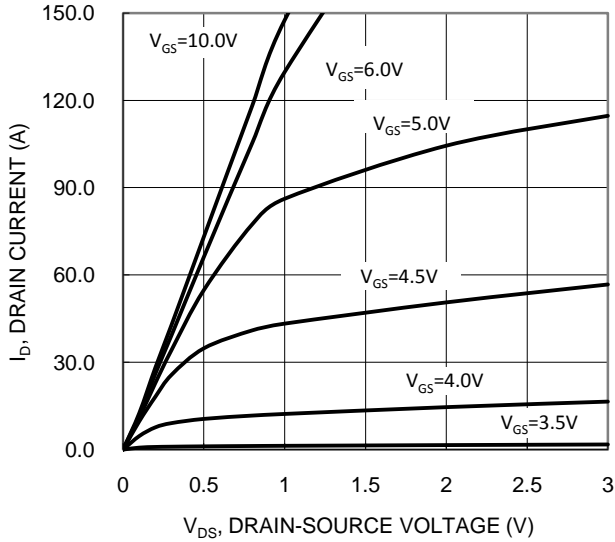


Figure 1. Typical Output Characteristic

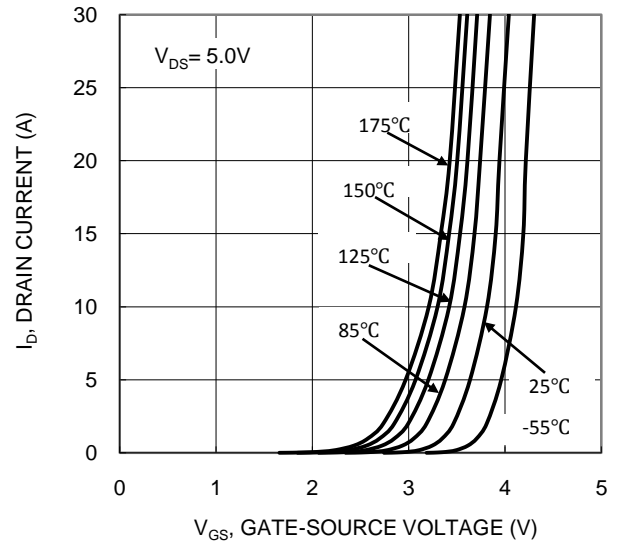


Figure 2. Typical Transfer Characteristic

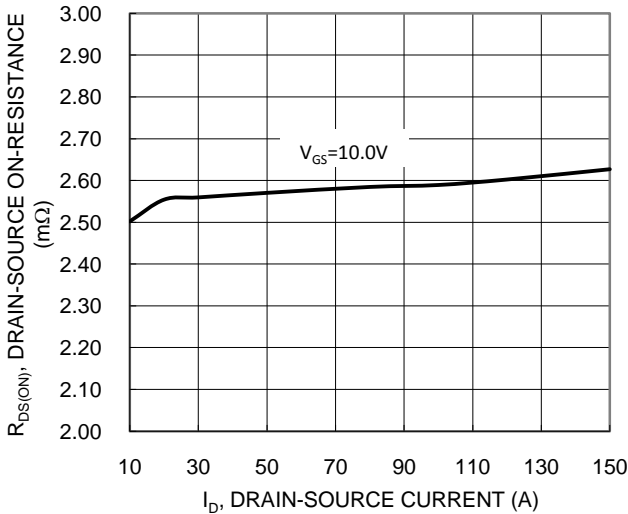


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

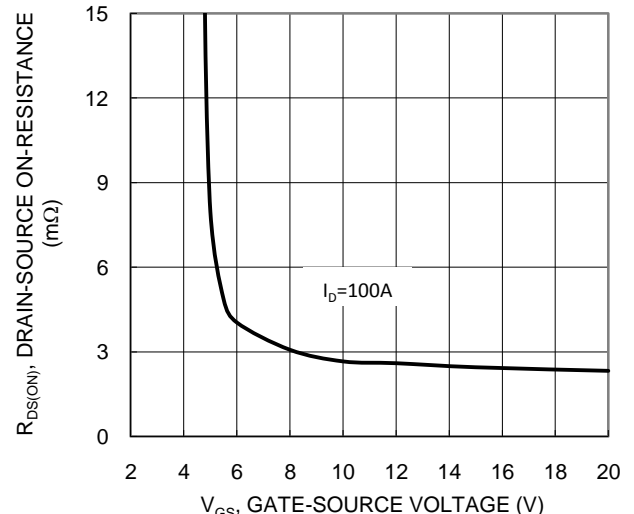


Figure 4. Typical Transfer Characteristic

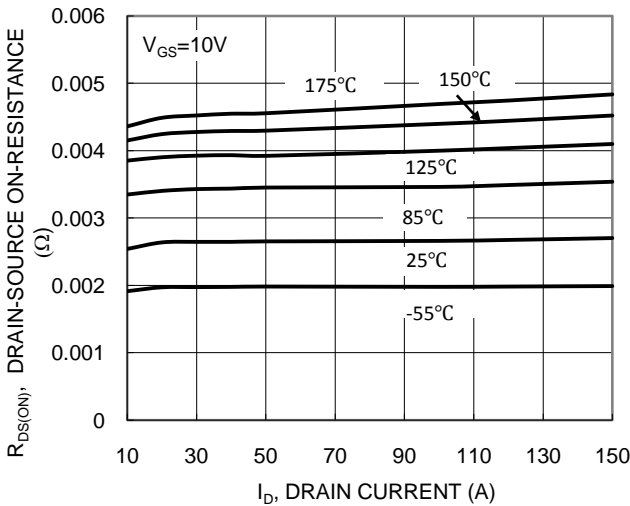


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

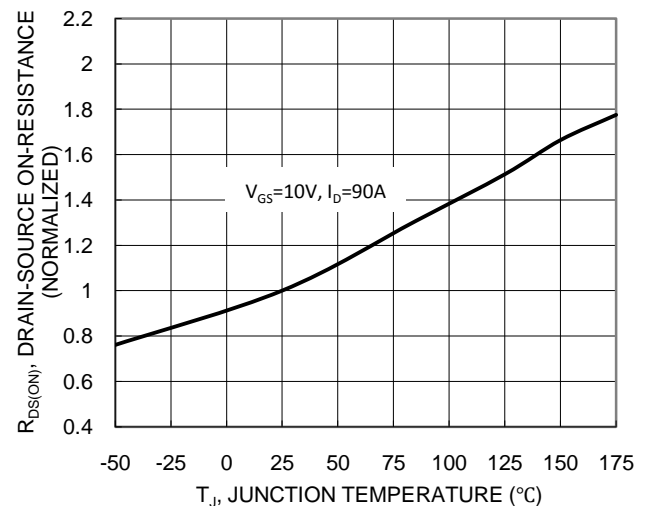


Figure 6. On-Resistance Variation with Temperature

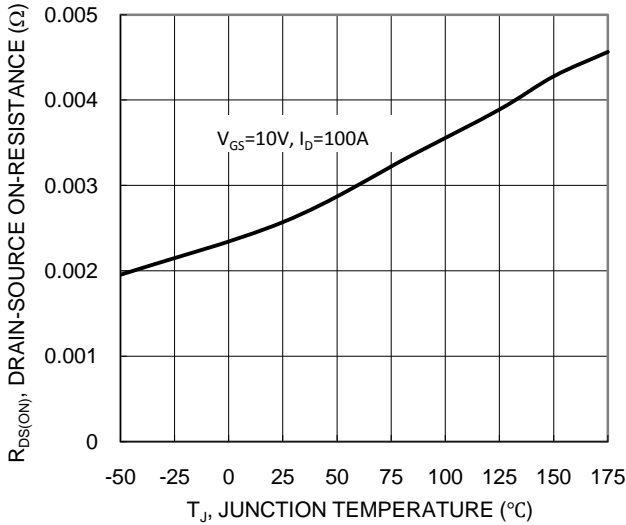


Figure 7. On-Resistance Variation with Temperature

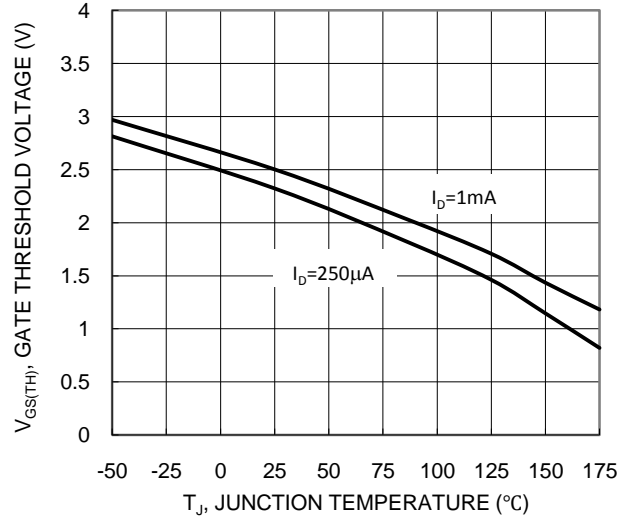


Figure 8. Gate Threshold Variation vs. Temperature

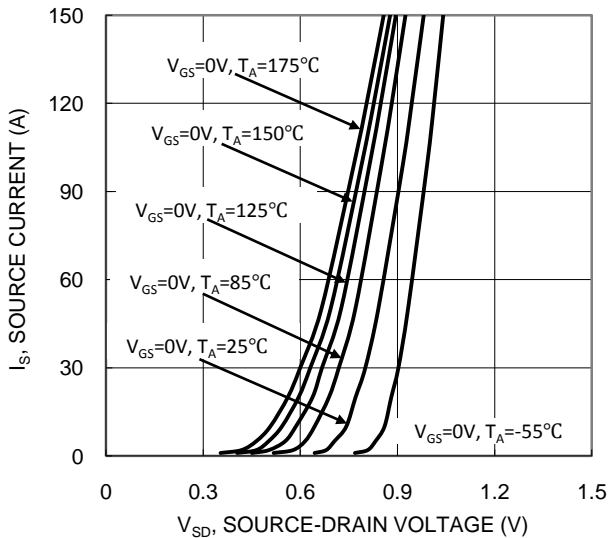


Figure 9. Diode Forward Voltage vs. Current

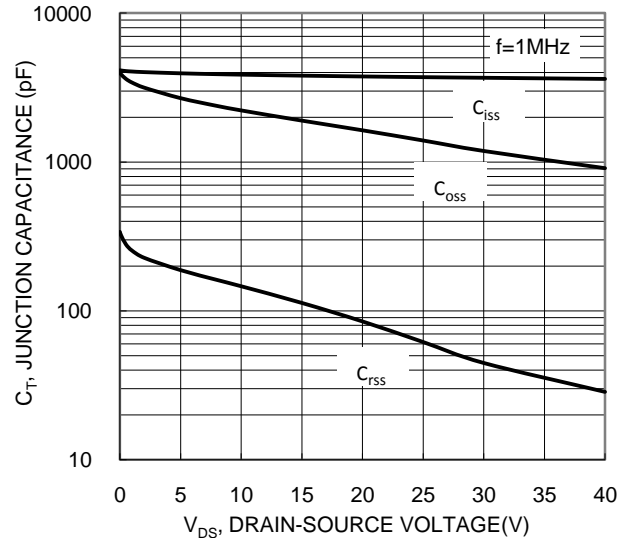


Figure 10. Typical Junction Capacitance

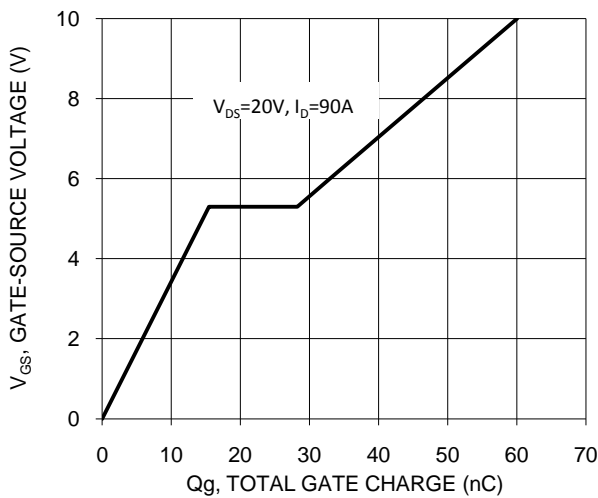


Figure 11. Gate Charge

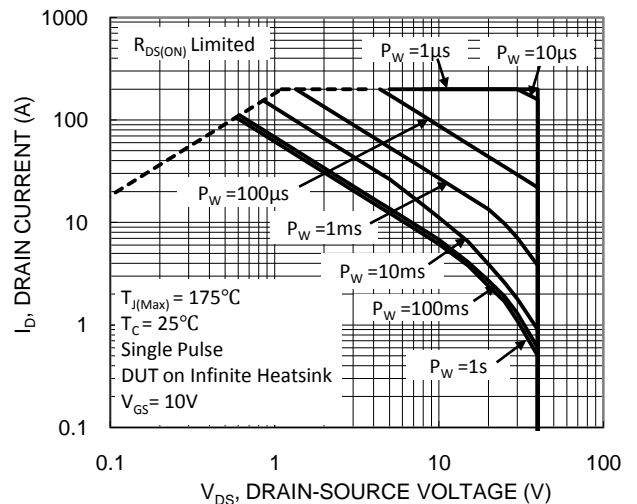


Figure 12. SOA, Safe Operation Area

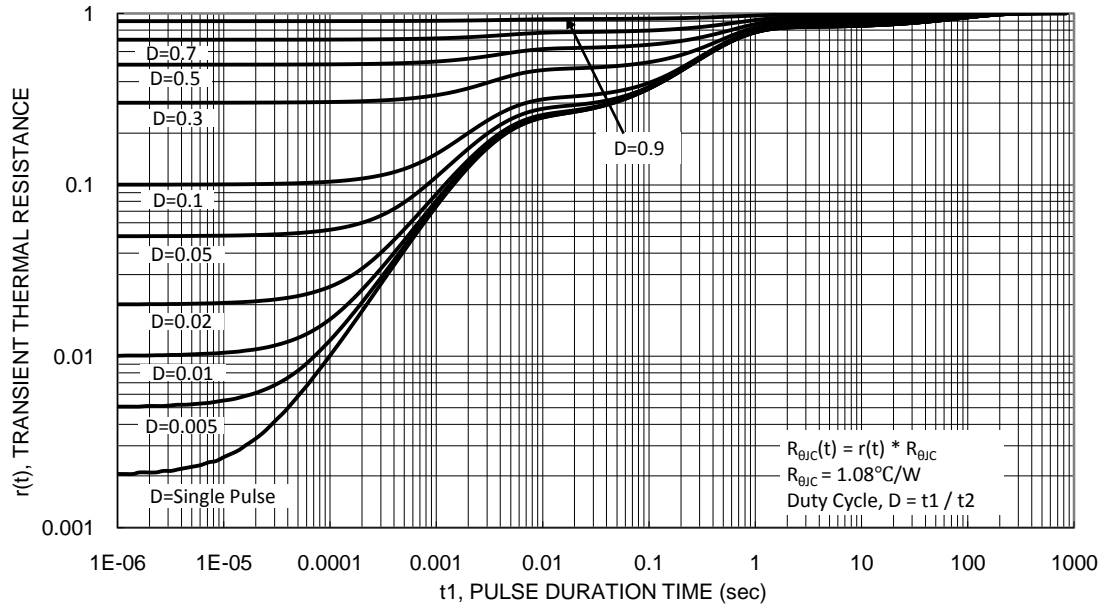
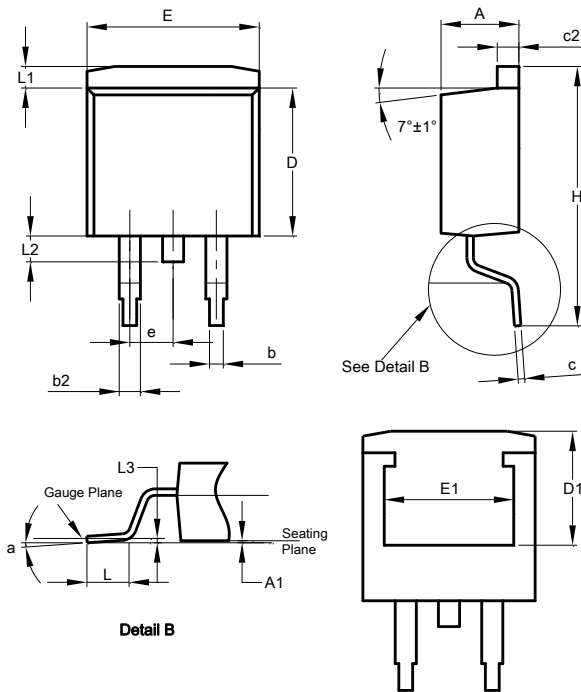


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

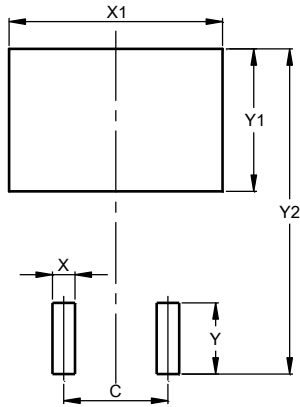
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO263AB (D2PAK)			
Dim	Min	Max	Typ
A	4.07	4.82	-
A1	0.00	0.25	-
b	0.51	0.99	-
b2	1.15	1.77	-
c	0.356	0.73	-
c2	1.143	1.65	-
D	8.39	9.65	-
D1	6.55	6.95	-
e	2.54 TYP		
E	9.66	10.66	-
E1	6.23	8.23	-
H	14.61	15.87	-
L	1.78	2.79	-
L1	-	1.67	-
L2	-	1.77	-
L3	-	-	0.254
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	5.08
X	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99

NEW PRODUCT

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